

Supporting Information

A Novel Water Developable Tetraphenyltin Based Nonchemically-Amplified Molecular Resist for Sub-13nm Lithography

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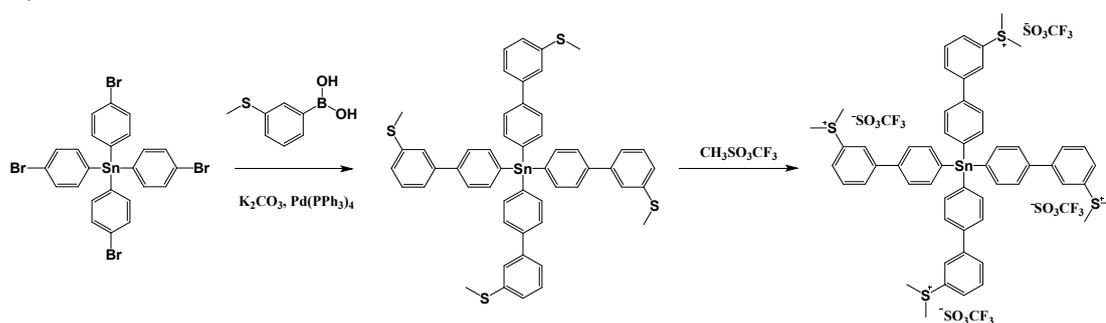
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1. Synthesis and Characterization of SnMS₄ and SnMSF₄



Scheme S1 Synthesis of SnMSF₄

Chemicals and Reagents. All the standard reagents and chemicals were purchased from commercial sources and used without any further purification. Sn(*p*-C₆H₄Br)₄ was synthesized according to the method reported in previous literature.^{1, 2}

Synthesis of tetrakis(3'-(methylthio)-[1,1'-biphenyl]-4-yl)stannane (SnMS₄). Sn(*p*-C₆H₄Br)₄ (4 g, 5.4 mmol), 3-methylthiophenylphenylboronic acid (5.44 g, 32.4 mmol), and anhydrous potassium carbonate (6.00 g, 43.4 mmol) were added to a 200 mL Schlenk flask, which was purged with argon and then charged with water (15 mL) and toluene (30 mL). Then tetratriphenylpalladium (0.40g, 0.35mmol) was added under a nitrogen atmosphere. The mixture was stirred at reflux overnight under a nitrogen atmosphere. The solution was cooled to room temperature and extracted with toluene/H₂O three times. The combined organic layer was washed with brine, and dried over Mg₂SO₄. The solvent was removed under vacuum, and the crude product was purified by column chromatography on silica gel (petroleum ether/CH₂Cl₂=1:1, v/v) to give SnMS₄ as a white solid (0.96 g, 19 %).¹H NMR (400 MHz, CD₂Cl₂) δ 7.76 (d, *J* = 8.1 Hz, 8H, benzene), 7.68 (d, *J* = 8.1 Hz, 8H, benzene), 7.51 (s, 4H, benzene), 7.43 – 7.35 (m, 8H, benzene), 7.30 – 7.22 (m, 4H, benzene), 2.53 (s, 12H, CH₃).**Synthesis of (stannanetetrayltetrakis([1,1'-biphenyl]-4',3-diyl))tetrakis (dimethylsulfonium)**

trifluoromethanesulfonate (SnMSF₄). SnMS₄ (0.24 g, 0.26 mmol) was added to a 250 mL round-bottomed flask with 120 mL dry CH₂Cl₂. Then methyl trifluoromethanesulfonate (0.52 g, 3.2 mmol) was added at room temperature. After stirring in the dark for 24 h, a large number of white solids were precipitated in the solution, which was filtered and washed with ether to give white solid of 0.38 g with a yield of 93%. ¹H NMR (400 MHz, CD₃CN) δ 8.19 (s, 4H, benzene), 8.09 (d, *J* = 7.9 Hz, 4H, benzene), 7.99 – 7.76 (m, 24H, benzene), 3.21 (s, 24H, CH₃). ¹⁹F NMR (600 MHz, CD₃CN) δ -79.29 (s, 1H). HRMS (ESI) *m/z*: [M]⁴⁺ calcd for C₅₆H₅₆S₄Sn⁴⁺ 244.0566, found 244.0566; [M]⁻ calcd for CF₃SO₃⁻ 148.9526, found 148.9525. FT-IR: *v*_{max}/cm⁻¹ 3061, 3024 and 2935 (CH), 1258 (CF₃), 1161 and 640 (SO₂), 1030 (S-O). Elemental analysis (%) calcd for C₆₀H₅₆F₁₂O₁₂S₈Sn: C, 45.84; H, 3.59; S, 16.31; found: C, 46.64; H, 3.68; S, 16.06.

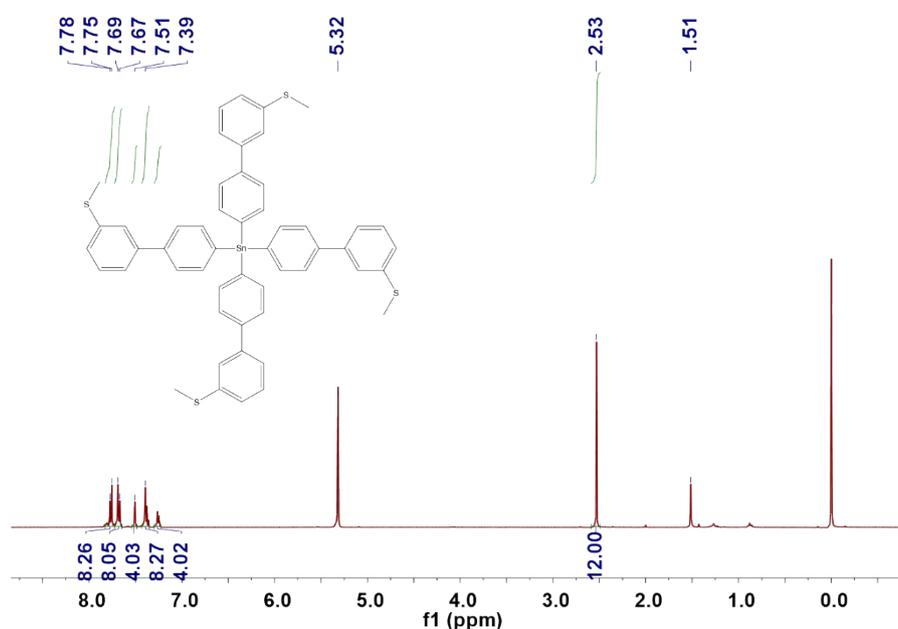


Figure S1. ¹H NMR (400 MHz, CD₂Cl₂) spectrum of SnMS.

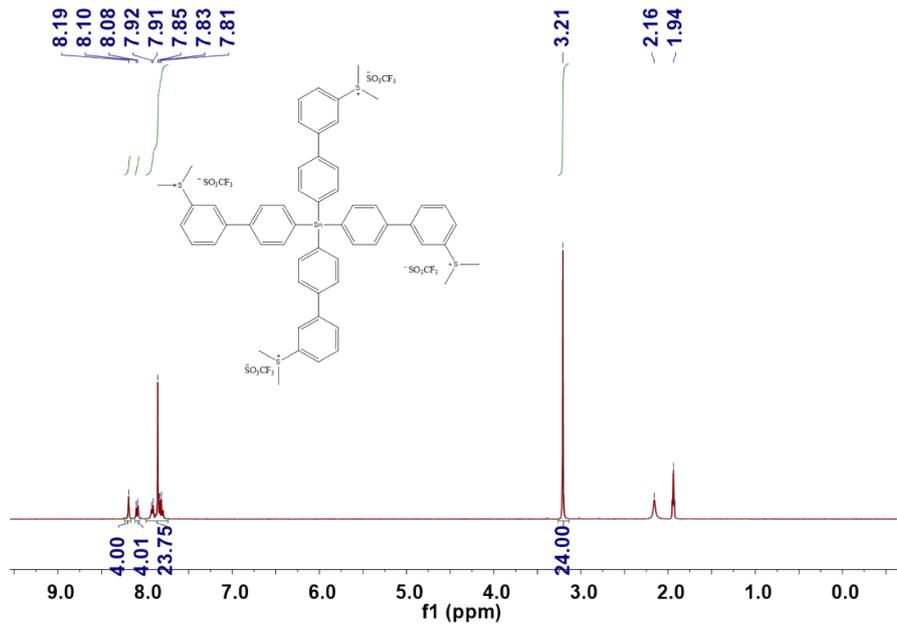


Figure S2. ^1H NMR (400 MHz, CD_3CN) spectrum of SnMSF_4 .

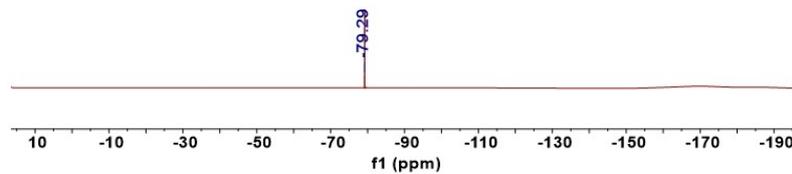


Figure S3. ^{19}F NMR (400 MHz, CD_3CN) spectrum of SnMSF_4 .

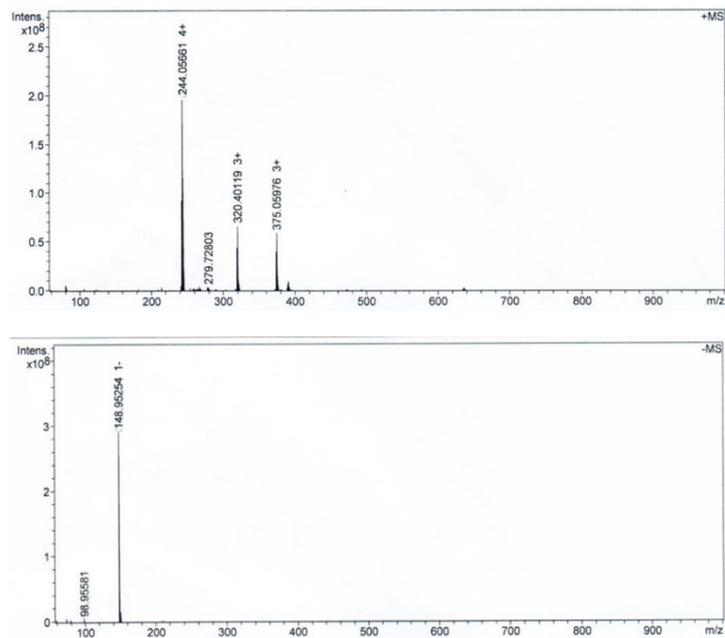


Figure S4. HRMS (ESI) spectrum of SnMSF_4 .

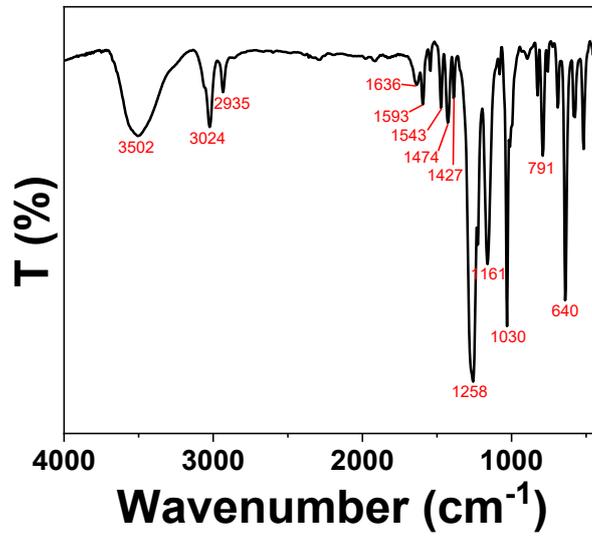


Figure S5. FT-IR spectrum of SnMSF₄.

2. Normalized remaining thickness (NRT) analysis

The contrast curves were obtained by fitting the film thickness data using a logistic function. According to the contrast curve, the tangent line at $y = 0.5$ can be obtained. The dose of tangent at $y = 0$ and 1 are considered as D_0 and D_{100} . The contrast could be calculated by the equation 1:

$$\gamma = \frac{1}{\log_{10}(D_{100}/D_0)} \quad (1)$$

3. EUV lithographic patterns with different exposure doses for SnMSF₄ resist

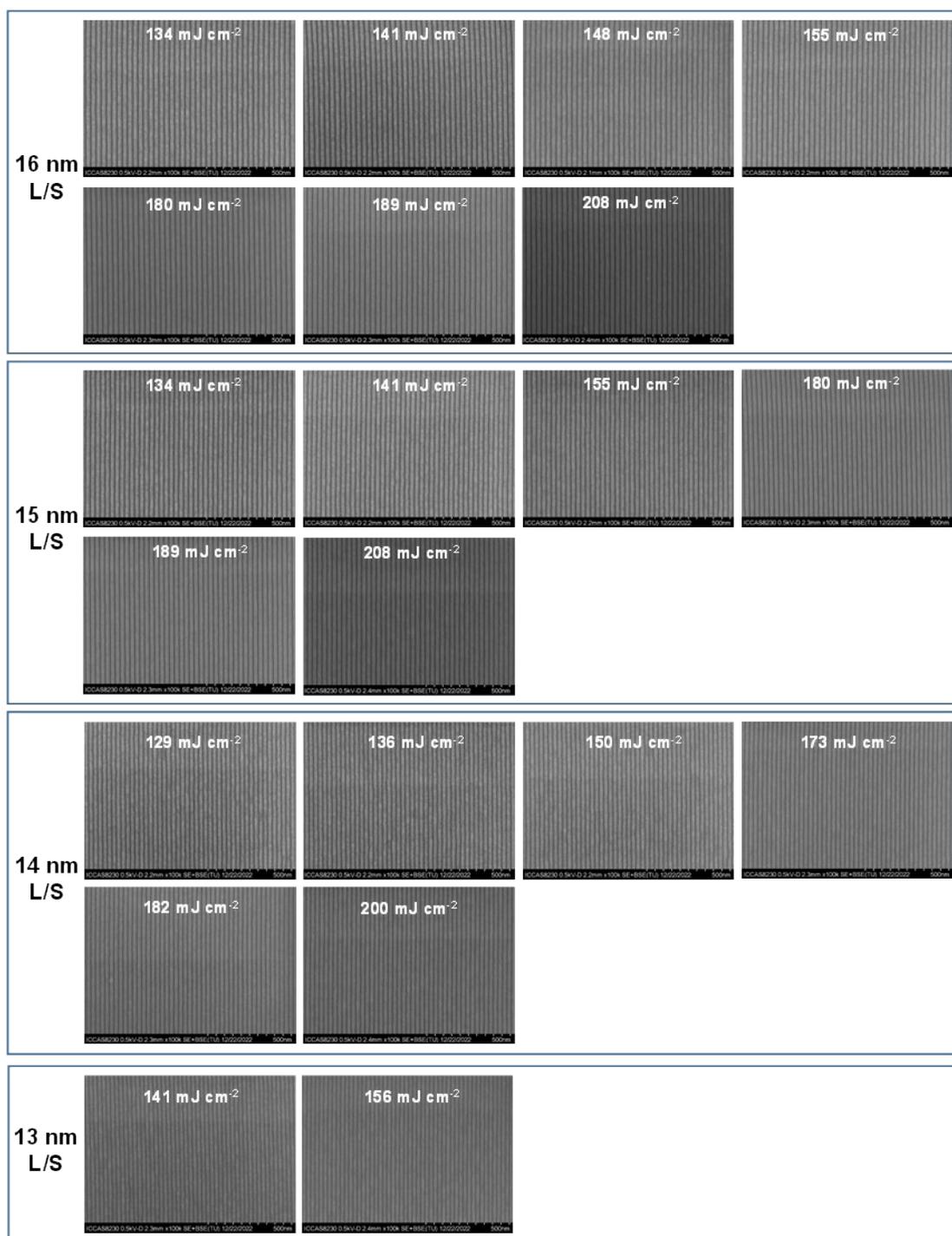


Figure S6. The 16, 15, 14 and 13 nm L/S line patterns of SnMSF₄ resist under different exposure doses for EUVL (Developer: H₂O).

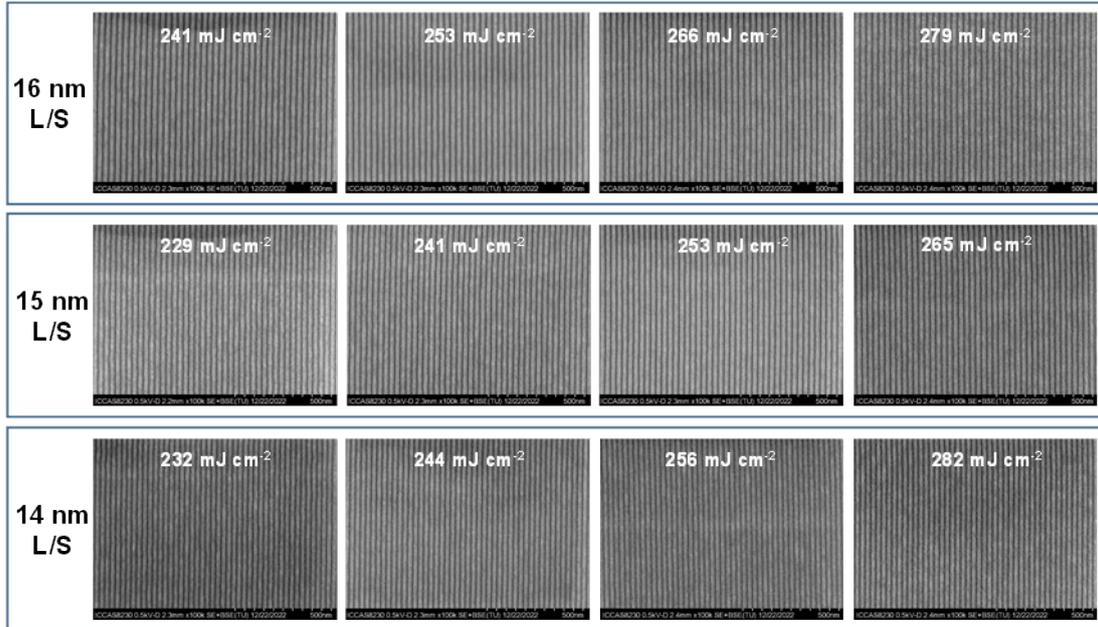


Figure S7. The 16, 15 and 14 nm L/S line patterns of SnMSF₄ resist under different exposure doses for EUVL (Developer: IPA/H₂O=1/10).

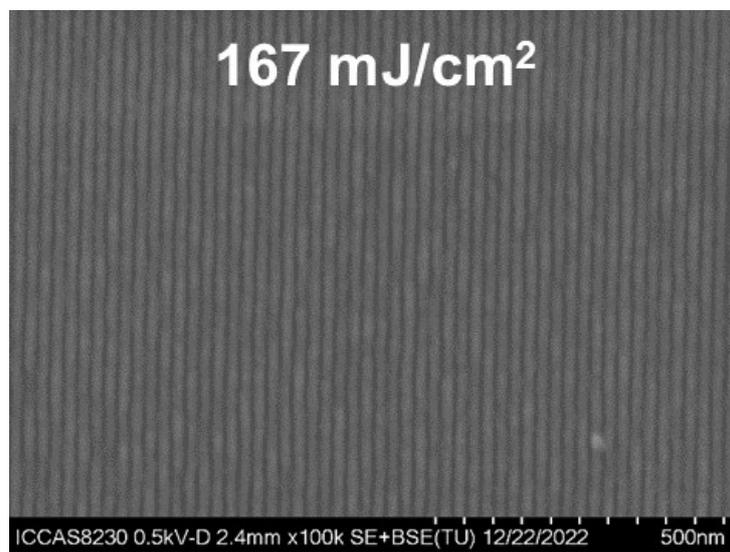


Figure S8 The 12 nm L/S line patterns of SnMSF₄ resist for EUVL (Developer: H₂O).

4. LER measurement of high-resolution SEM images

The information on the SEM images was listed as following:

Data Size = 1280x960; Pixel Size=0.9921876; Signal Name=SE+BSE(TU);

Magnification = 100000

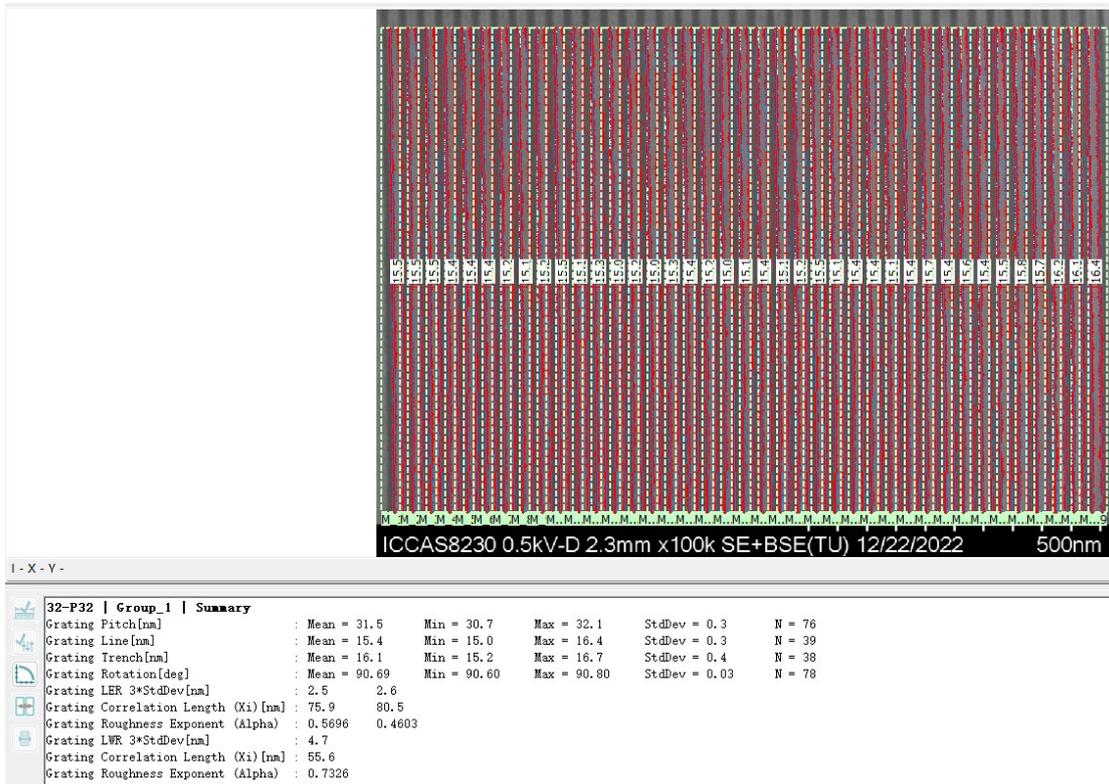


Figure S9. The LER and LWR measurement of 16 nm L/S pattern of SnMSF₄ resist (Developer: H₂O).

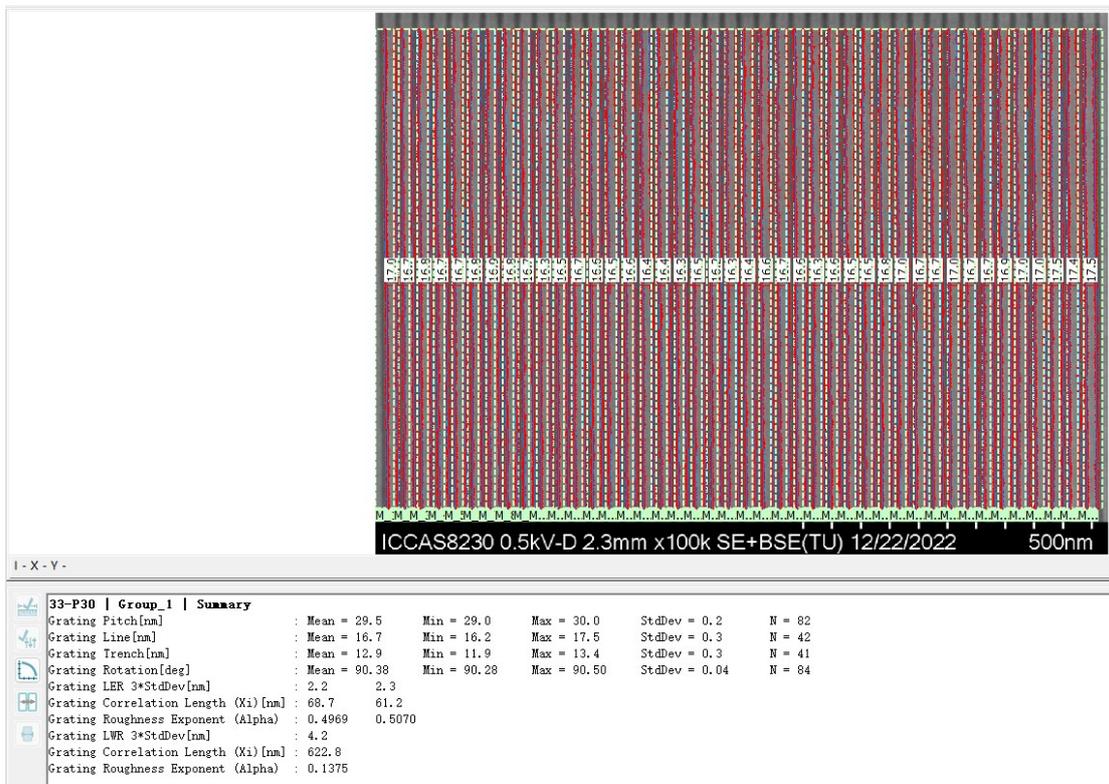


Figure S10. The LER and LWR measurement of 15 nm L/S pattern of SnMSF₄ resist (Developer: H₂O).

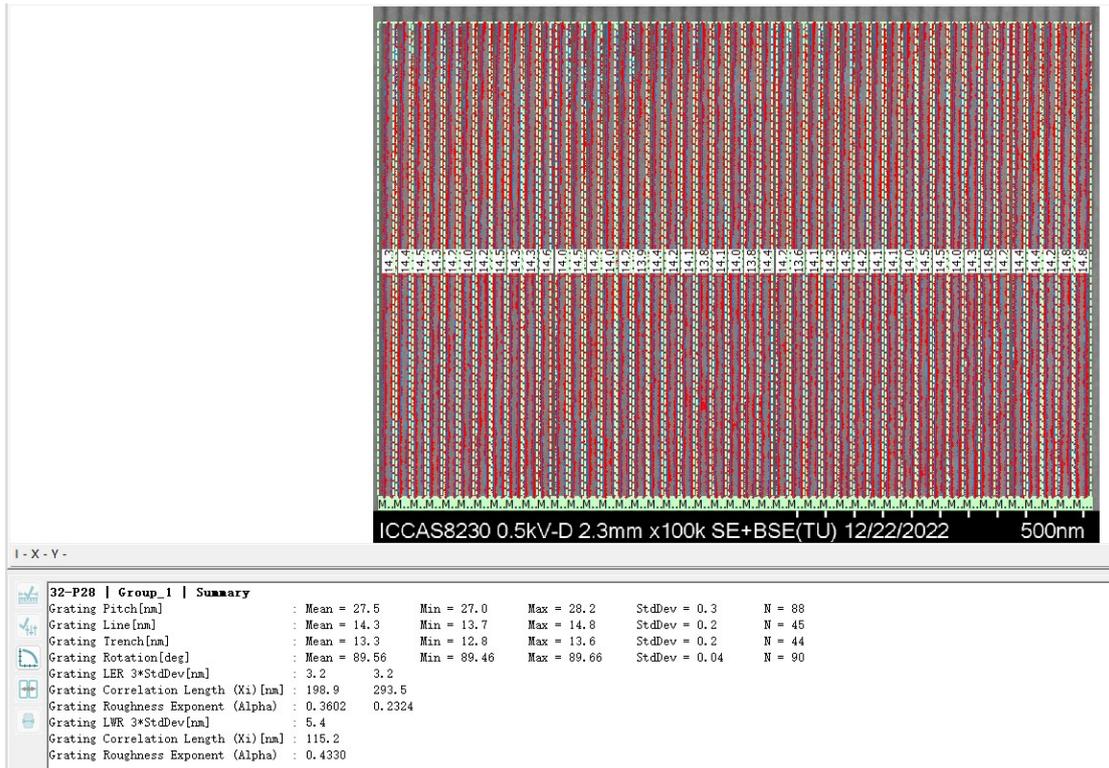


Figure S11. The LER and LWR measurement of 14 nm L/S pattern of SnMSF₄ resist (Developer: H₂O).

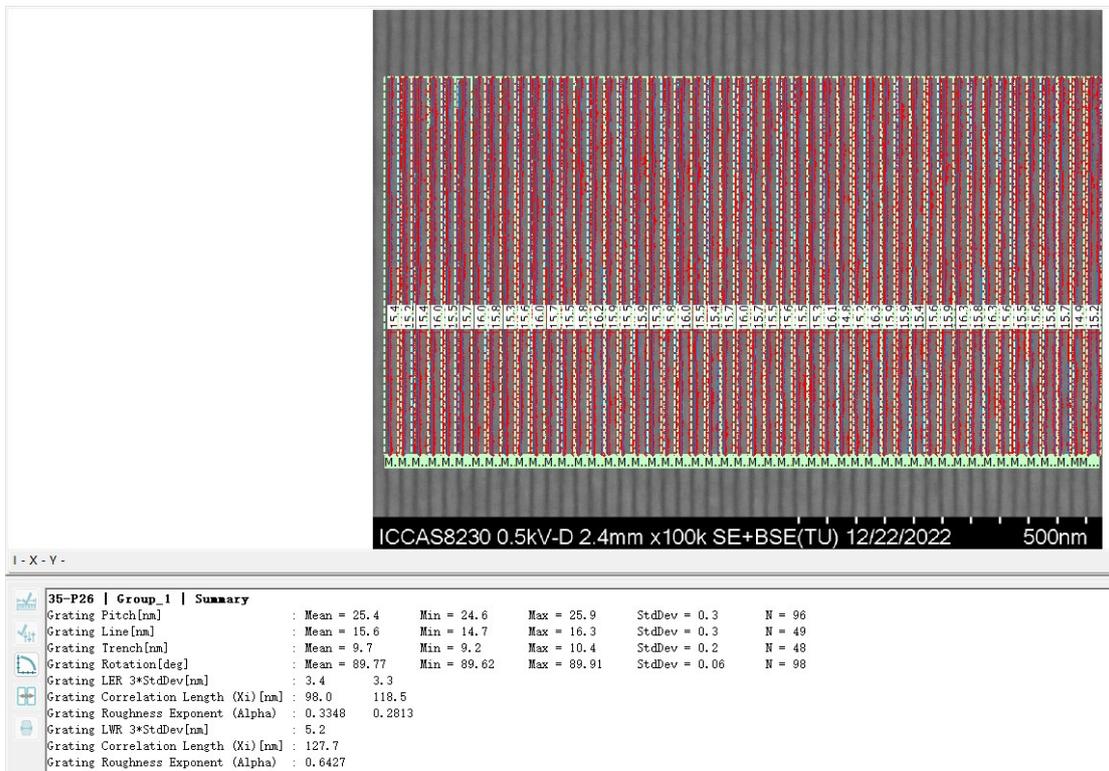


Figure S12. The LER and LWR measurement of 13 nm L/S pattern of SnMSF₄ resist (Developer: H₂O).

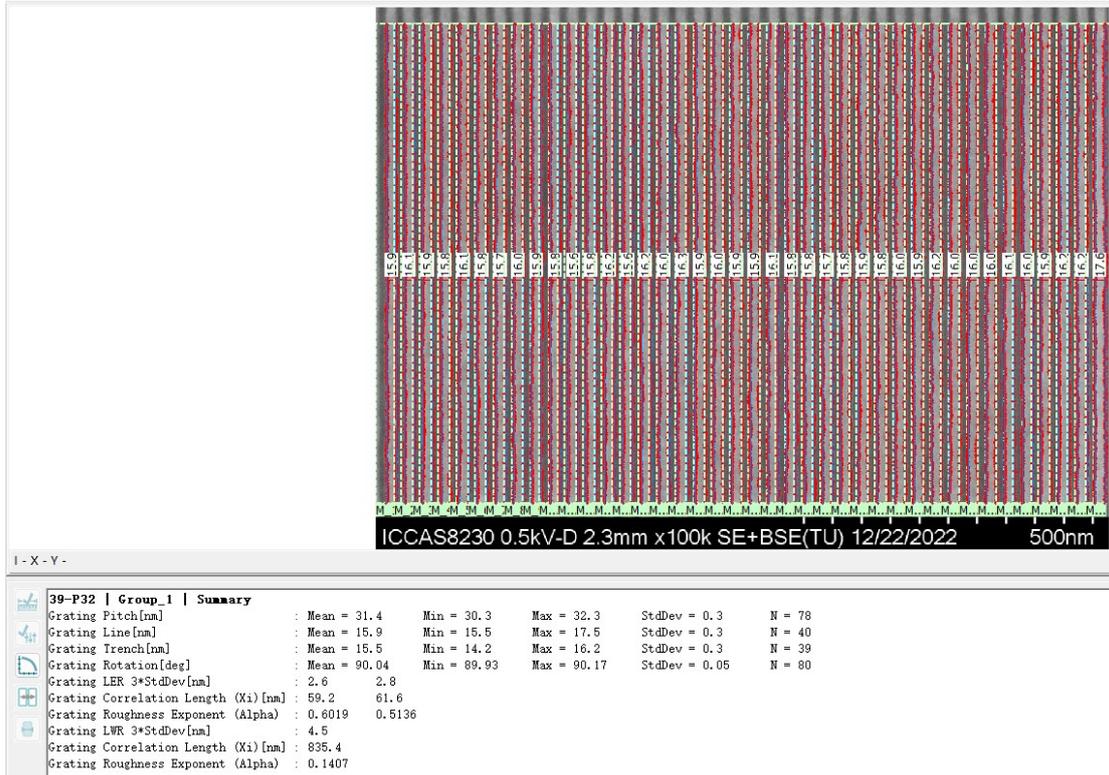


Figure S13. The LER and LWR measurement of 16 nm L/S pattern of SnMSF₄ resist (Developer: IPA/H₂O=1/10).

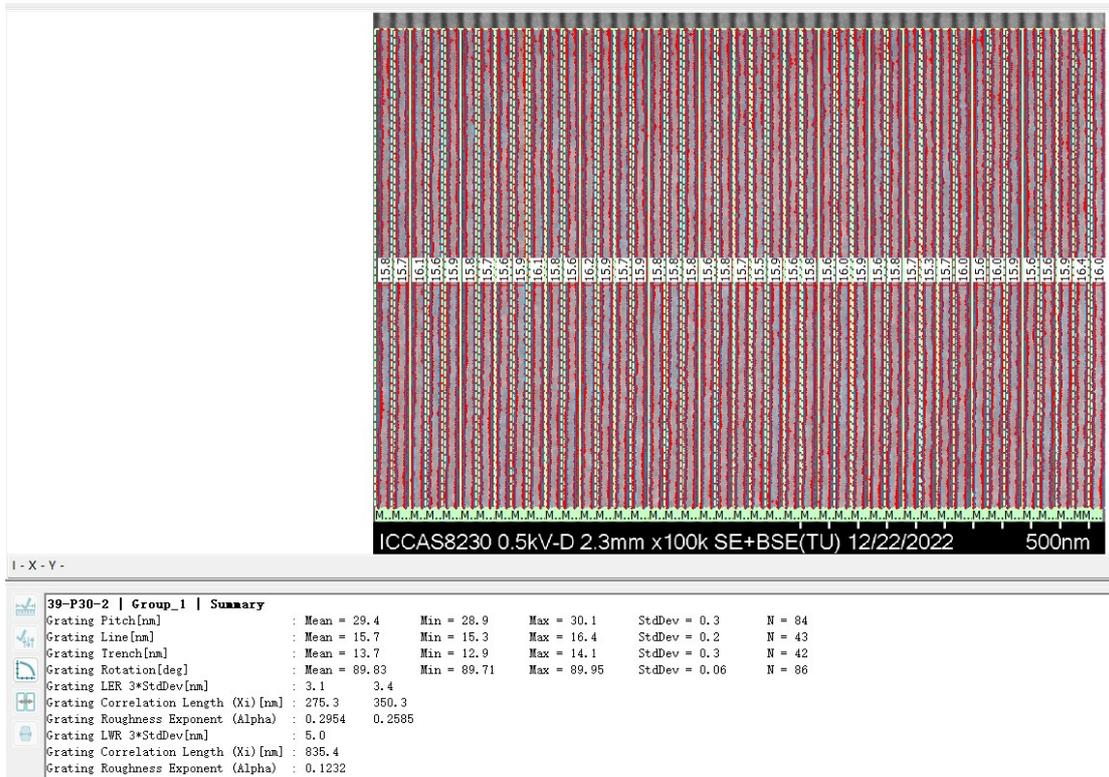


Figure S14. The LER and LWR measurement of 15 nm L/S pattern of SnMSF₄ resist (Developer: IPA/H₂O=1/10).

5. XPS test results for mechanism analysis

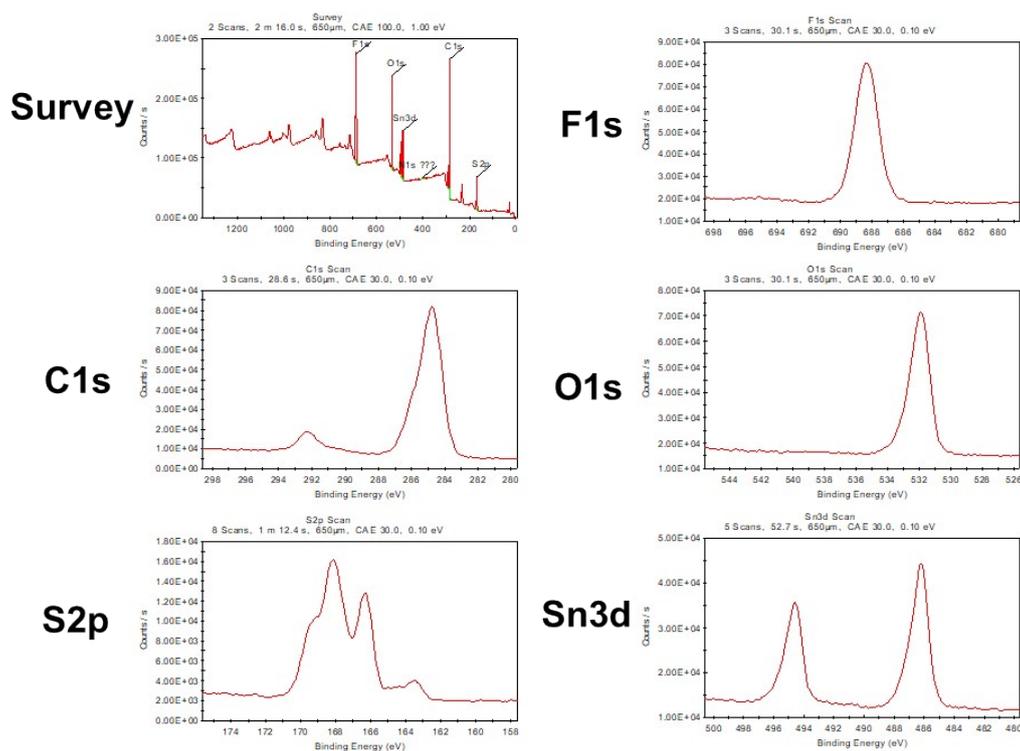


Figure S15. The XPS survey spectra and high-resolution XPS spectra of C 1s, S 2p, F 1s, O 1s and Sn 3d for the pristine film of SnMSF₄ resist.

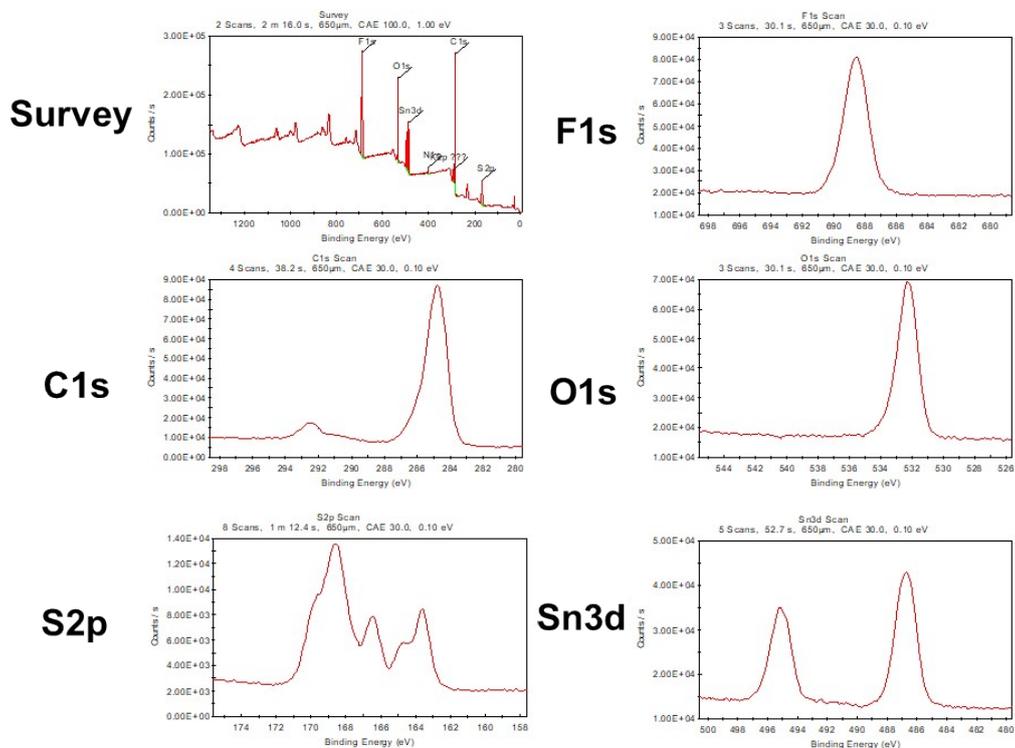


Figure S16. The XPS survey spectra and high-resolution XPS spectra of C 1s, S 2p, F 1s, O 1s and Sn 3d for the SnMSF₄ resist films after e-beam exposure.

1. Yang, Y.; Beele, B.; Bluemel, J., Easily immobilized di- and tetraphosphine linkers: Rigid scaffolds that prevent interactions of metal complexes with oxide supports. *Journal of the American Chemical Society* **2008**, *130* (12), 3771-3773.
2. Uptmoor, A. C.; Geyer, F. L.; Rominger, F.; Freudenberg, J.; Bunz, U. H. F., Tetrahedral Tetrakis(p-ethynylphenyl) Group IV Compounds in Microporous Polymers: Effect of Tetrel on Porosity. *Chempluschem* **2018**, *83* (5), 448-454.